

In the Specification:

The paragraph beginning on page 1, line 15 has been rewritten to read as follows:

$\beta^1$  --For the purpose of lowering the resistance offered by an interconnection layer, the feasibility of substituting a Cu interconnection layer for the conventional Al interconnection layer has been the subject of a diligent study. Cu has lower resistivity than Al and about twice as high electromigration resistance as Al.--

The paragraph beginning on page 1, line 22 has been rewritten to read as follows:

$\beta^2$  --Generally, the formation of a layer of fine wiring lines requires resorting to dry etching.--

The paragraph beginning on page 4, line 22 has been rewritten to read as follows:

$\beta^3$  --In contrast, in the CVD-TiN layer with excellent step coverage, substantially no oxygen was detected except on the surface as shown in Fig. 2B. This contrast may be logically explained by a supposition that since the PVD-TiN layer had small crystal grain particles are compared with the CVD-TiN layer, the former layer permitted easier entrance of oxygen from the ambient air than the latter layer.--